

COMPLIANT



## High Voltage, Single and Dual Supply SPDT Analog Switch with Enable Pin

#### **DESCRIPTION**

The DG469, DG470 are high voltage SPDT switches, with a typical on resistance of 3.6  $\Omega$  and typical flatness of 0.4  $\Omega$ . The DG469, DG470 are identical, except the DG470 provides an enable input. When the enable input is activated, both sides of the switch are in a high impedance mode (Off), maintaining a "Safe State" at power up. This function can also be used as a quick "disconnect" in the event of a fault condition. For audio switching, the enable pin provides a mute function. These are high voltage switches that are fully specified with dual supplies at  $\pm$  4.5 V and  $\pm$  15 V and a single supply of 12 V over an operating temperature range from - 40 °C to + 125 °C. Fast switching speeds coupled with high signal bandwidth makes these parts suitable for video switching applications. All digital inputs have 0.8 V and 2.4 V logic thresholds ensuring low voltage TTL/CMOS compatibility. Each switch conducts equally well in both directions when on and can handle an input signal range that extends to the supply voltage rails. They exhibit breakbefore-make switching action to prevent momentary shorting when switching between channels. The DG469, DG470 are offered in a MSOP 8 and SOIC 8 package.

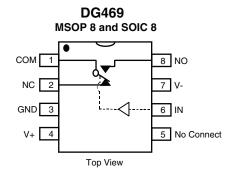
#### **FEATURES**

- Low on resistance (3.6 Ω typical)
- On resistance flatness (0.4 Ω typical)
- 44 V supply maximum rating
- ± 15 V analog signal range
- Fully specified at supply voltages of  $\pm$  4.5 V, 12 V and  $\pm$  15 V
- TTL/CMOS compatible
- · Break before make switching guaranteed
- Total harmonic distortion 0.0145 %
- · Compliant to RoHS Directive 2002/95/EC

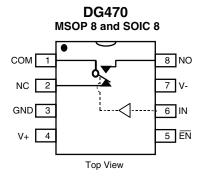
#### **APPLICATIONS**

- Audio and video signal switching
- · Precision automatic test equipment
- · Precision data acquisition
- · Relay replacement
- Communications systems
- · Automotive applications
- · Sample and hold systems
- · Power routing applications
- Telecom signal switching
- · Medical equipment
- · Portable and battery power systems

#### **FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION**



TRUTH TABLE DG469						
Logic	NC	NO				
0	ON	OFF				
1	OFF	ON				



TRUTH TABLE DG470								
ENABLE	Logic	NC	NO					
0	0	ON	OFF					
0	1	OFF	ON					
1	X	OFF	OFF					



ORDERING INFORMATION							
Temp. Range	Package	Part Number					
DG469, DG470							
10.00 . 105.008	8-Pin MSOP	DG469EQ-T1-E3 DG470EQ-T1-E3					
- 40 °C to 125 °C <sup>a</sup>	8-Pin Narrow SOIC	DG469EY-T1-E3 DG470EY-T1-E3					

#### Notes:

a. - 40 °C to 85 °C datasheet limits apply.

Parameter		Limit	Unit		
V+ to V-	44				
GND to V-	25				
Digital Inputs <sup>a</sup> , V <sub>S</sub> , V <sub>D</sub>		(V-) - 2 to (V+) + 2 or 30 mA, whichever occurs first	V		
Continuous Current (NO, NC, or COM)		120			
Current (Any terminal except NO, NC, or COM)		30	mA		
Peak Current, (Pulsed 1 ms, 10 % Duty Cycle	)	200			
Storage Temperature		- 65 to 150	°C		
Danier Diagination (Dadraga)	8-Pin MSOP <sup>c</sup>	320	mW		
Power Dissipation (Package) <sup>b</sup>	8-Pin Narrow SOIC <sup>d</sup>	400	1 mvv		

#### Notes:

- $a. \ Signals \ on \ S_X, \ D_X, \ or \ IN_X \ exceeding \ V+ \ or \ V- \ will \ be \ clamped \ by \ internal \ diodes. \ Limit forward \ diode \ current \ to \ maximum \ current \ ratings.$
- b. All leads welded or soldered to PC board.
- c. Derate 4.0 mW/°C above 70 °C. d. Derate 5.0 mW/°C above 70 °C.

SPECIFICATIONS for Dual Supplies									
		Test Conditions			- 40 °C t	- 40 °C to 125 °C   - 40 °C to 85			
Parameter	Symbol	Unless Specified V+ = 15 V, V- = - 15 V V <sub>IN</sub> = 2.4 V, 0.8 V <sup>a</sup>	Temp.b	Typ. <sup>c</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	Unit
Analog Switch									
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full		- 15	15	- 15	15	V
On-Resistance	R <sub>ON</sub>	$I_S = 50 \text{ mA}, V_D = -10 \text{ V to} + 10 \text{ V}$	Room Full	3.6		6 8		6 7	
On-Resistance Match	ΔR <sub>ON</sub>	$I_S = 50 \text{ mA}, V_D = \pm 10 \text{ V}$	Room Full	0.12		0.4 0.9		0.4 0.5	Ω
On-Resistance Flatness	R <sub>FLATNESS</sub>	$I_S = 50 \text{ mA}, V_D = -5 \text{ V}, 0 \text{ V}, +5 \text{ V}$	Room Full	0.4		0.5 0.9		0.5 0.8	
Switch Off	I <sub>S(off)</sub>	V <sub>D</sub> = ± 14 V, V <sub>S</sub> = ± 14 V	Room Full	± 0.1	- 0.5 - 20	0.5 20	- 0.5 - 2.5	0.5 2.5	
Leakage Current	I <sub>D(off)</sub>	VD - ± 1+ V, VS - ± 1+ V	Room Full	± 0.1	- 0.5 - 20	0.5 20	- 0.5 - 2.5	0.5 2.5	nA
Channel On Leakage Current	I <sub>D(on)</sub>	$V_{S} = V_{D} = \pm 14 \text{ V}$	Room Full	± 0.2	- 0.5 - 20	0.5 20	- 0.5 - 5	0.5 5	
Digital Control									
Input Current, V <sub>IN</sub> Low	I <sub>IL</sub>	V <sub>IN</sub> Under Test = 0.8 V	Full	0.05	- 1	1	- 1	1	μΑ
Input Current, V <sub>IN</sub> High	I <sub>IH</sub>	V <sub>IN</sub> Under Test = 2.4 V	Full	0.05	- 1	1	- 1	1	μΑ
Input Capacitance <sup>e</sup>	C <sub>IN</sub>	f = 1 MHz	Room	3.7					pF



SPECIFICATIONS for Dual Supplies									
		Test Conditions			- 40 °C t	o 125 °C	- 40 °C	to 85 °C	
Parameter	Symbol	Unless Specified V+ = 15 V, V- = - 15 V V <sub>IN</sub> = 2.4 V, 0.8 V <sup>a</sup>	Temp.b	Typ. <sup>c</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	Unit
Dynamic Characteristics									
Turn-On Time	t <sub>ON</sub>	$R_L = 300 \Omega$ , $C_L = 35 pF$	Room Full	129		166 200		166 185	
Turn-Off Time	t <sub>OFF</sub>	$V_S = \pm 10 \text{ V}$	Room Full	80		108 135		108 120	ns
Break-Before-Make Time Delay	t <sub>D</sub>	$V_S = 10 \text{ V}$ $R_L = 300 \Omega, C_L = 35 \text{ pF}$	Room	15					
Charge Injection <sup>e</sup>	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 1 \text{ nF}$	Room	58					рC
Off Isolation <sup>e</sup>	OIRR	$R_L = 50 \Omega, C_L = 5 pF$	Room	- 57					
Channel-to-Channel Crosstalk <sup>e</sup>	X <sub>TALK</sub>	f = 1 MHz	Room	- 63					dB
Source Off Capacitance <sup>e</sup>	C <sub>S(off)</sub>		Room	37					
Drain Off Capacitance <sup>e</sup>	C <sub>D(off)</sub>	f = 1 MHz	Room	85					pF
Channel On Capacitance <sup>e</sup>	C <sub>D(on)</sub>		Room	125					
Power Supplies									
Power Supply Current	I+		Room Full	3.0		6 7		6 7	
Negative Supply Current	I-	V+ = 16.5 V, V- = -16.5 V $V_{IN} = 0 \text{ or } 5 V$	Room Full	- 0.4	- 0.5 - 4.5		- 0.5 - 4.5		μΑ
Ground Current	I <sub>GND</sub>		Room Full	- 3.0	- 6 - 7		- 6 - 7		

SPECIFICATIONS for Dual Supplies									
		Test Conditions			- 45 °C to 125 °C		- 40 °C to 85 °C		
P	0	Unless Specified V+ = 4.5 V, V- = - 4.5 V V <sub>IN</sub> = 2.4 V, 0.8 V <sup>a</sup>	h	C	aa: d	d	na: d	aa d	
Parameter Analog Switch	Symbol	V <sub>IN</sub> = 2.4 V, 0.6 V	Temp.b	Typ. <sup>c</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	Unit
	V		Full		- 4.5	4.5	- 4.5	4.5	V
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>				- 4.5		- 4.5		V
On-Resistance <sup>e</sup>	R <sub>ON</sub>	$I_S = 50 \text{ mA}, V_D = -2 \text{ V to} + 2 \text{ V}$	Room Full	8		11 16		11 15	Ω
On-Resistance Match <sup>e</sup>	ΔR <sub>ON</sub>	$I_S = 50 \text{ mA}, V_D = \pm 2 \text{ V}$	Room Full	0.6		0.7 0.9		0.7 0.8	52
<b>Dynamic Characteristics</b>			1			•	I.	·	
Turn-On Time <sup>e</sup>	t <sub>ON</sub>	$R_L$ = 300 Ω, $C_L$ = 35 pF	Room Full	245		265 340		65 310	
Turn-Off Time <sup>e</sup>	t <sub>OFF</sub>	V <sub>S</sub> = 2 V	Room Full	145		163 200		163 185	ns
Break-Before-Make <sup>e</sup> Time Delay	t <sub>D</sub>	$V_S = 2 V$ $R_L = 300 \Omega, C_L = 35 pF$	Room Full	15					
Charge Injection <sup>e</sup>	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 1 \text{ nF}$	Full	58					рС
Power Supplies									
Power Supply Current <sup>e</sup>	l+		Room Full	3.0		6 7		6 7	
Negative Supply Current <sup>e</sup>	l-	$V_{IN} = 0$ or 4.5 V	Room Full	- 0.4	- 0.5 - 4.5		- 0.5 - 4.5		μΑ
Ground Current <sup>e</sup>	I <sub>GND</sub>		Room Full	3.0	- 6 - 7		- 6 - 7		



SPECIFICATIONS for Unipolar Supplies									
		Test Conditions Unless Specified			- 40 °C t	o 125 °C	- 40 °C	to 85 °C	
		V+ = 12 V, V- = 0 V	_ h	_ ^	d	d	d	d	
Parameter	Symbol	$V_{IN} = 2.4 \text{ V}, 0.8 \text{ V}^{a}$	Temp.b	Typ. <sup>c</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	Unit
Analog Switch									
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full			12		12	V
On-Resistance	R <sub>ON</sub>	$I_S = 25 \text{ mA}, V_D = 0 \text{ V to} + 10 \text{ V}$	Room Full	7.5		8.5 14		8.5 11.3	
On-Resistance Match	ΔR <sub>ON</sub>	$I_S = 25 \text{ mA}, V_D = + 10 \text{ V}$	Room Full	0.4		0.45 0.9		0.45 0.5	Ω
On-Resistance Flatness	R <sub>FLATNESS</sub>	$I_S = 25 \text{ mA},$ $V_D = 0 \text{ V}, + 5 \text{ V}, + 10 \text{ V}$	Room Full	2.5		2.6 2.9		2.6 2.8	
Dynamic Characteristics	•								
Turn-On Time	t <sub>ON</sub>	$R_L = 300 \Omega, C_L = 35 pF$	Room Full	190		200 255		200 240	
Turn-Off Time	t <sub>OFF</sub>	V <sub>S</sub> = 10 V	Room Full	100		110 135		110 120	ns
Break-Before-Make Time Delay	t <sub>D</sub>	$V_S = 10 \text{ V}$ $R_L = 300 \Omega, C_L = 35 \text{ pF}$	Room	50					
Charge Injection <sup>e</sup>	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 1 \text{ nF}$	Room	2.4					рC
Power Supplies	Power Supplies								
Power Supply Current	I+		Room Full	3.0		6 7		6 7	
Negative Supply Current	I-	V <sub>IN</sub> = 0 or 5 V	Room Full	- 0.4	- 0.5 - 4.5		- 0.5 - 4.5		μΑ
Ground Current	I <sub>GND</sub>		Room Full	- 3.0	- 6 - 7		- 6 - 7		

#### Notes:

- a.  $V_{IN}$  = input voltage to perform proper function.
- b. Room = 25  $^{\circ}$ C, Full = as determined by the operating temperature suffix.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- e. Guaranteed by design, not subject to production test.

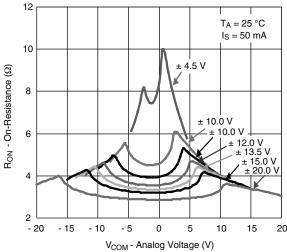
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

28

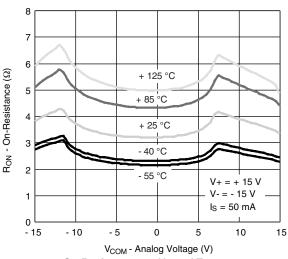
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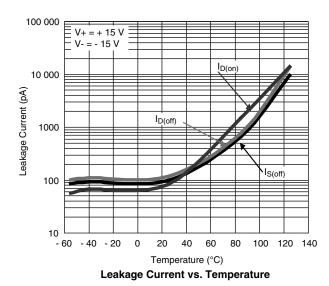
#### **TYPICAL CHARACTERISTICS**



On-Resistance vs.  $V_{\rm D}$  and Dual Supply Voltage



On-Resistance vs. V<sub>D</sub> and Temperature



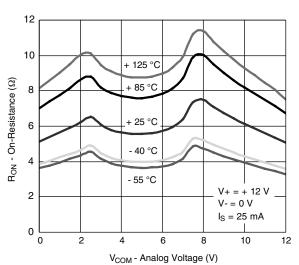
14 13 T<sub>A</sub> = 25 °C + 7.0 V I<sub>S</sub> = 25 mA 12 + 9.0 V 11 + 10.8 V R<sub>ON</sub> - On-Resistance (Ω) 10 + 12.0 V 9 8 + 20.0 V + 24.0 V + 36.0 V 4

3

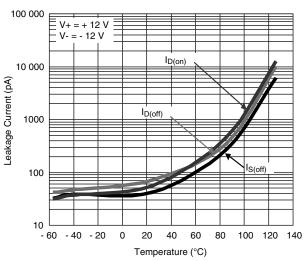
0

 $\label{eq:VCOM} \mbox{$^{\prime}$} V_{COM} \mbox{$^{\prime}$} \mbox{$^{\prime}$} Analog \mbox{ Voltage (V)} \\ \mbox{On-Resistance vs. } V_{\mbox{$D$}} \mbox{ and Single Supply Voltage}$ 

16



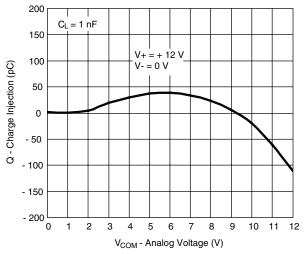
On-Resistance vs. V<sub>D</sub> and Temperature



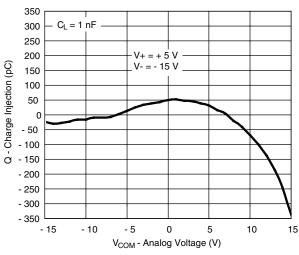
Leakage Current vs. Temperature

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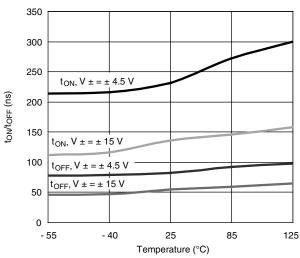
#### **TYPICAL CHARACTERISTICS**



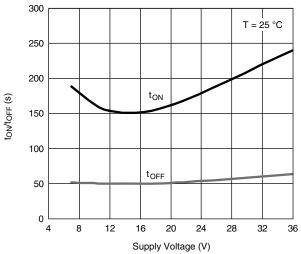
Charge Injection vs. Analog Voltage



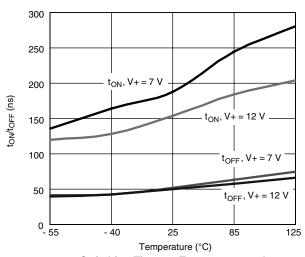
Charge Injection vs. Analog Voltage



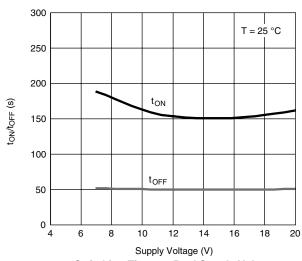
Switching Time vs. Temperature and Dual Supply Voltage



Switching Time vs. Single Supply Voltage



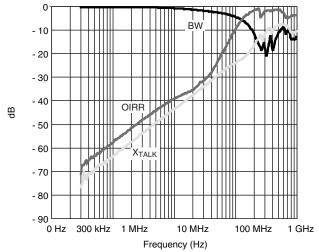
Switching Time vs. Temperature and Single Supply Voltage



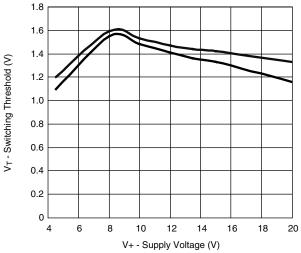
Switching Time vs. Dual Supply Voltage



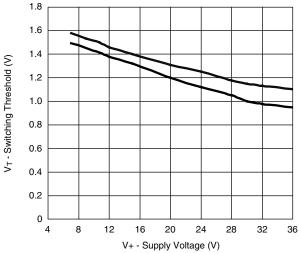
#### **TYPICAL CHARACTERISTICS**



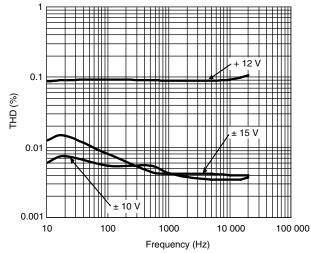
Insertion Loss, Off-Isolation, Crosstalk vs. Frequency



Switching Threshold vs. Dual Supply Voltage

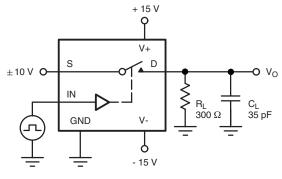


Switching Threshold vs. Signal Supply Voltage



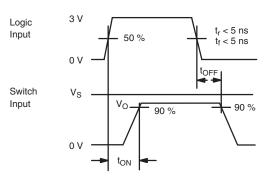
DG469, DG470 Total Harmonic Distortion

#### **TEST CIRCUITS**



C<sub>L</sub> (includes fixture and stray capacitance)

$$V_{O} = V_{S}$$
 
$$\frac{R_{L}}{R_{L} + r_{DS(on)}}$$

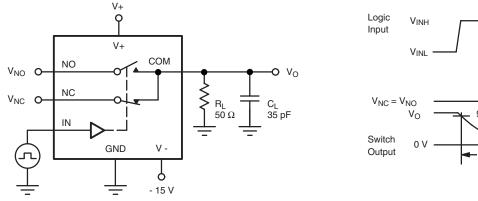


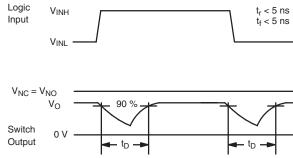
Note: Logic input waveform is inverted for switches that have the opposite logic sense control.

Figure 1. Switching Time

#### **TEST CIRCUITS**







C<sub>L</sub> (includes fixture and stray capacitance)

Figure 2. Break-Before-Make

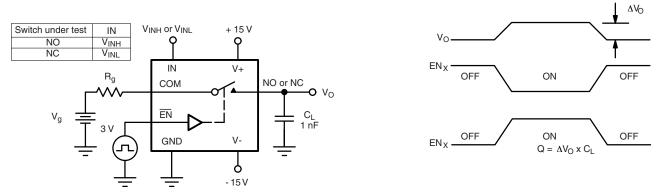
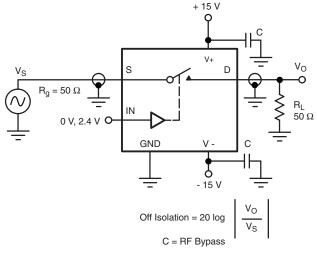


Figure 3. Charge Injection





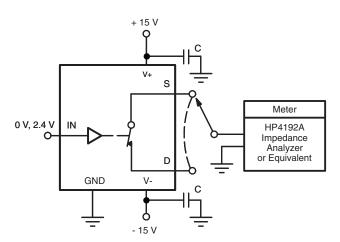


Figure 5. Source/Drain Capacitances

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Vishay

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